

A B S T R A C T

A DEVICE FOR IMPROVING THE MOBILITY OF CARRIERS IN A
MOSFET CHANNEL ON SILICON CARBIDE

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The present invention relates to a MOSFET device arranged on a substrate 10 comprising first and second heavily-doped strips 11 and 14 respectively covered by first and second contacts 13 and 15, these two strips
10 being spaced apart by a channel 18 that also appears on the substrate 10, the channel being covered by a dielectric layer 20, itself surmounted by a third contact 21.

The device is remarkable in that the channel 18
15 incorporates a thin film 19 lightly doped with dopant atoms of a same type as the channel, at the interface with the dielectric layer 20, the dopant atoms being distributed on both sides of the interface.

20 [Sole figure]